Title (en)

METHOD FOR PRODUCING AN INTEGRATED CIRCUIT COMPRISING A CAVITY IN A MATERIAL LAYER AND INTEGRATED CIRCUIT PRODUCED USING SAID METHOD

Title (de)

VERFAHREN ZUR HERSTELLUNG EINER INTEGRIERTEN SCHALTUNGSANORDNUNG UMFASSEND EINEN HOHLRAUM IN EINER MATERIALSCHICHT, SOWIE EINE DURCH DAS VERFAHREN ERZEUGTE INTEGRIERTE SCHALTUNGSANORDNUNG

Title (fr)

PROCEDE PERMETTANT DE FORMER UN CIRCUIT INTEGRE COMPRENANT UNE CAVITE DANS UNE COUCHE DE MATERIAU ET CIRCUIT INTEGRE FABRIQUE SELON LEDIT PROCEDE

Publication

EP 1101389 B1 20080924 (DE)

Application

EP 99945888 A 19990702

Priority

- DE 9902041 W 19990702
- DE 19830535 A 19980708

Abstract (en)

[origin: WO0003560A2] The recess is produced in a material layer (S) by creating at least a first (S1) and a second structure (S2) in various steps. Said layers define each other laterally and extend to the bottom of the recess. The first structure (S1) and the second structure (S2) are so narrow that they can be made by creating conformally produced layers (F1, F2) that have an independent thickness and are smaller than the depth of said recess. The conformally produced layers (F1, F2) are formed in an appropriate deposition process. A covering structure can be produced on top of the first (S1) and second structure (S2). An opening can be made in said covering structure, through which the first structure (S1) and the second structure (S2) can be removed in an etching step.

IPC 8 full level

G01P 15/08 (2006.01); **H04R 19/00** (2006.01); **G01L 9/00** (2006.01); **H01L 21/3105** (2006.01); **H01L 21/762** (2006.01); **H01L 29/84** (2006.01); **H04R 19/04** (2006.01); **H04R 31/00** (2006.01)

CPC (source: EP US)

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